

Silicon PNP Power Transistors

2SB1392

DESCRIPTION

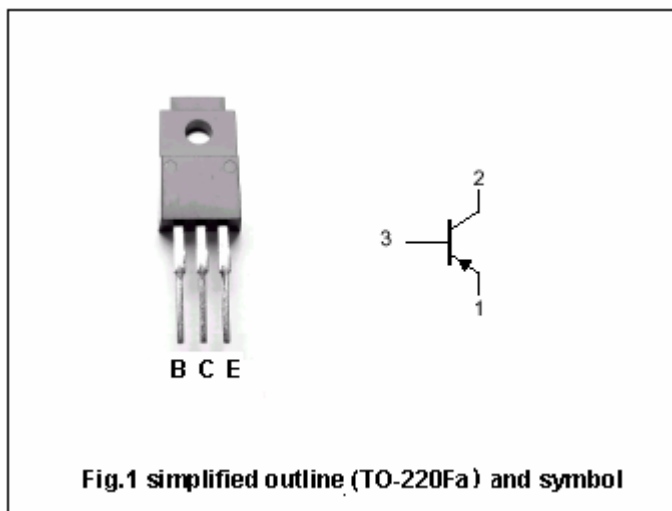
- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	-70	V
V _{CEO}	Collector -emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-4	A
I _{CM}	Collector current-peak		-8	A
P _C	Collector power dissipation	T _a =25°C	2.0	W
		T _C =25°C	25	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; R _{BE} =∞	-60			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10μA; I _E =0	-70			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10μA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-1.2	V
V _{BE}	Base-emitter voltage	I _C =-1A; V _{CE} =-4V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V; I _E =0			-10	μA
I _{CEO}	Collector cut-off current	V _{CE} =-50V; R _{BE} =∞			-10	μA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-4V	60		200	
h _{FE-2}	DC current gain	I _C =-0.1A; V _{CE} =-4V	35			

◆ h_{FE-1} classifications

B	C
60-120	100-200

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PACKAGE OUTLINE

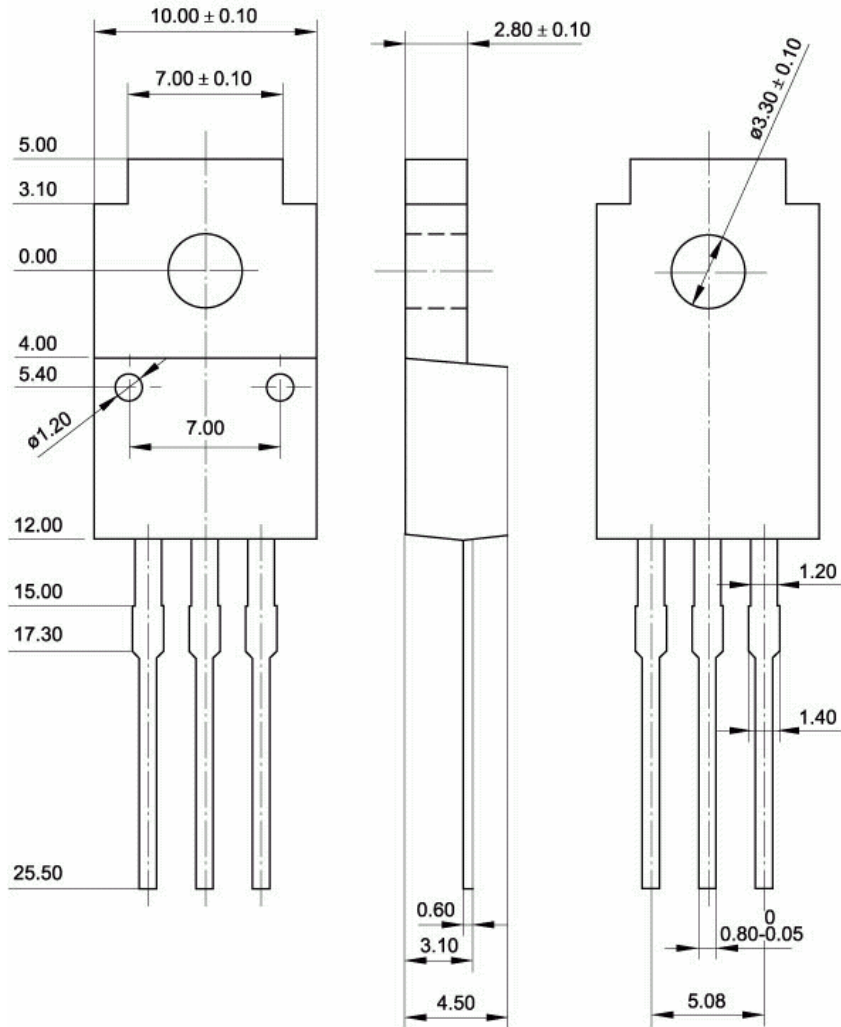


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)